

ABSTRACT

An object of the invention is to provide a target member for physical vapor deposition, in
5 which deterioration of a underlayer due to oxidation is little in forming a physically vapor-
deposited film, there appear few defects at a junction between the physically vapor-deposited
film and the underlayer, the lattice matching between the physically vapor-deposited film and the
underlayer is good, and further deterioration in quality due to hydration of the target member
itself or the physically vapor-deposited film to be formed is little. The target member for
10 physical vapor deposition contains Mg, M (M is a trivalent metal element), and O as main
components, in which the molar ratio of Mg to M in terms of the oxides of MgO and M_2O_3
respectively is 70:30 to 10:90.